

Transistor

2.5V Drive Pch MOS FET

RTQ030P02

●Structure

Silicon P-channel MOSFET

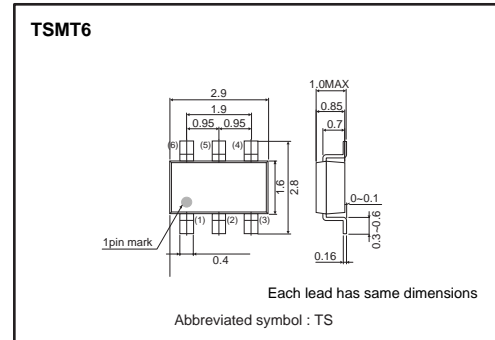
●Features

- 1) Low On-resistance.(110mΩ at 2.5V)
- 2) High Power Package.
- 3) High speed switching.
- 4) Low voltage drive.(2.5V)

●Applications

DC-DC converter

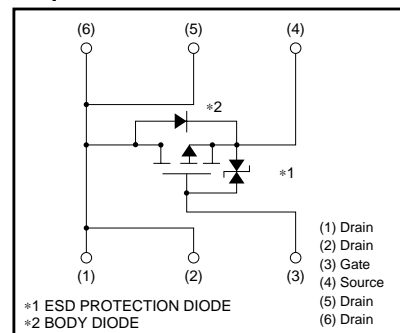
●External dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RTQ030P02		○

●Equivalent circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	-20	V
Gate-source voltage	V_{GS}	±12	V
Drain current	Continuous	I_D	±3 A
	Pulsed	I_{DP} *1	±12 A
Source current (Body diode)	Continuous	I_S	-1 A
	Pulsed	I_{SP} *1	-4 A
Total power dissipation	P_D *2	1.25	W
Channel temperature	T_{ch}	150	°C
Range of Storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10\mu s$, Duty cycle ≤ 1%
 *2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	100	°C / W

* Mounted on a ceramic board.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	–20	–	–	V	I _D =–1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	–1	μA	V _{DS} =–20V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	–0.7	–	–2.0	V	V _{DS} =–10V, I _D =–1mA
Static drain-source on-state resistance	R _{DS(on)} [*]	–	60	80	mΩ	I _D =–3A, V _{GS} =–4.5V
		–	65	90	mΩ	I _D =–3A, V _{GS} =–4V
		–	110	150	mΩ	I _D =–1.5A, V _{GS} =–2.5V
Forward transfer admittance	Y _{fs} [*]	2.0	–	–	S	V _{DS} =–10V, I _D =–1.5A
Input capacitance	C _{iss}	–	800	–	pF	V _{DS} =–10V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}	–	150	–	pF	
Reverse transfer capacitance	C _{rss}	–	100	–	pF	
Turn-on delay time	t _{d(on)} [*]	–	15	–	ns	I _D =–1.5A V _{DD} =–15V V _{GS} =–4.5V R _L =10Ω R _G =10Ω
Rise time	t _r [*]	–	27	–	ns	
Turn-off delay time	t _{d(off)} [*]	–	50	–	ns	
Fall time	t _f [*]	–	20	–	ns	
Total gate charge	Q _g	–	9.0	–	nC	V _{DD} =–15V V _{GS} =–4.5V I _D =–3A
Gate-source charge	Q _{gs}	–	1.6	–	nC	
Gate-drain charge	Q _{gd}	–	4.6	–	nC	

*PULSED

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	–	–	–1.2	V	I _S =–1A, V _{GS} =0V

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●Electrical characteristic curves

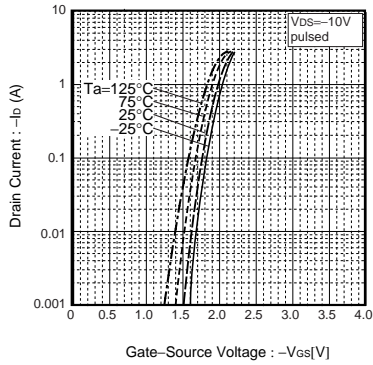


Fig.1 Typical Transfer Characteristics

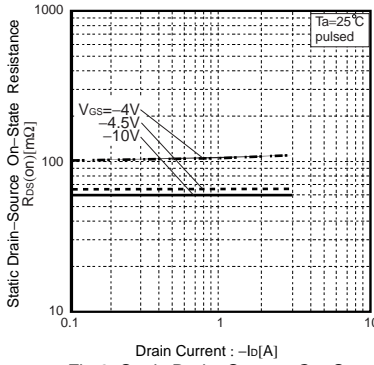


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

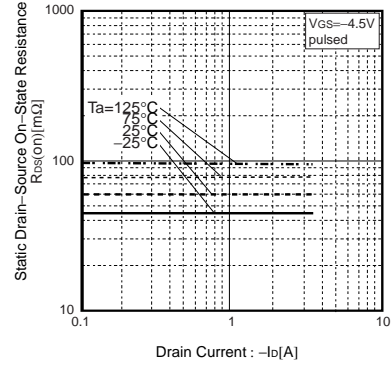


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

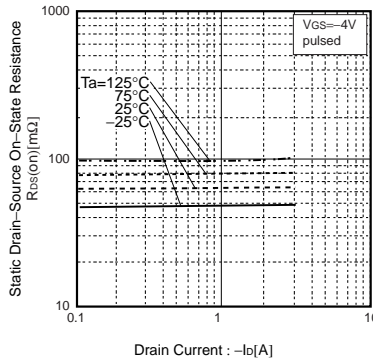


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

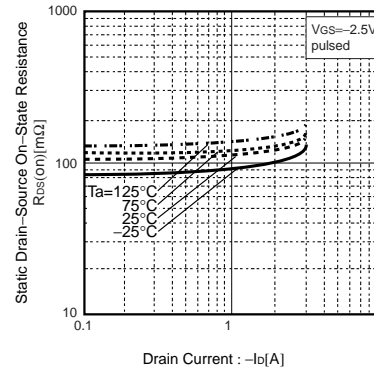


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

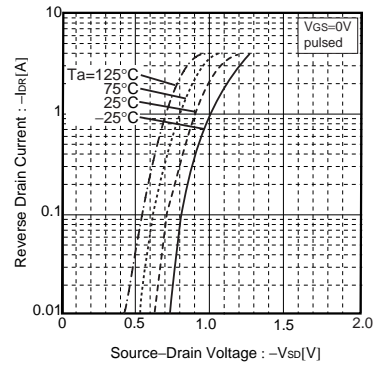


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

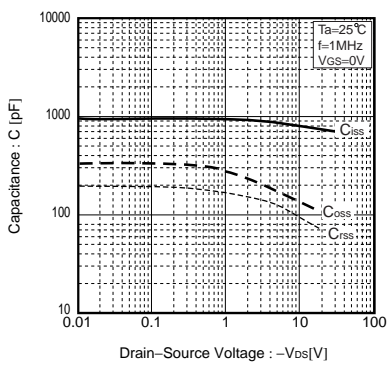


Fig.7 Typical Capacitance vs. Drain-Source Voltage

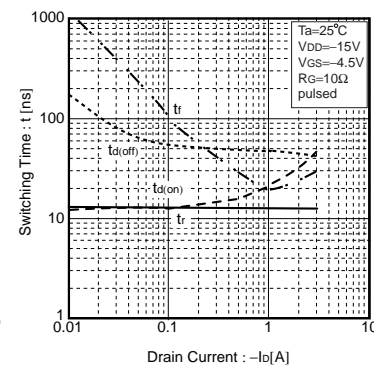


Fig.8 Switching Characteristics

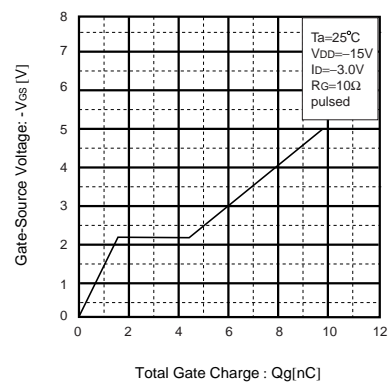


Fig.9 Dynamic Input Characteristics

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●Measurement circuits

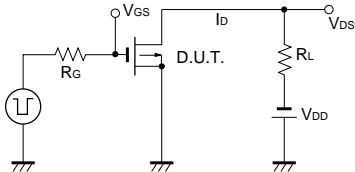


Fig.10 Switching Time Measurement Circuit

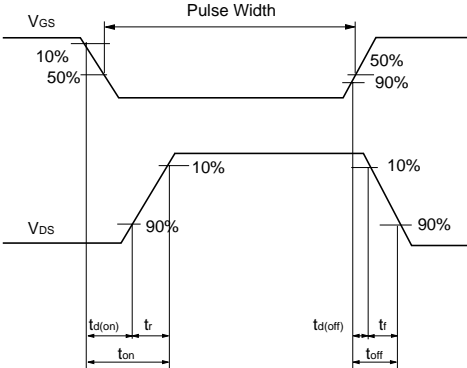


Fig.11 Switching Waveforms

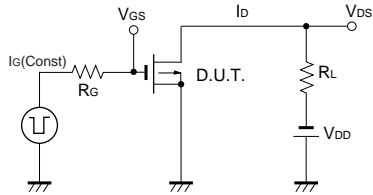


Fig.12 Gate Charge Measurement Circuit

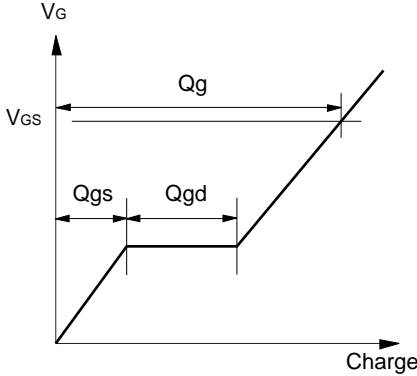


Fig.13 Gate Charge Waveforms

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